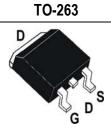
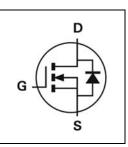


60V N-Channel Power MOSFET

 V_{DSS} , 60V $R_{\text{DS(ON)}}$, $4.3m\Omega$ (max.) @ $V_{\text{GS}}\text{=}10V$ I_{D} , 136A





Description	Features
The SG60N03G uses advanced Trench technology and designs to provide excellent R _{DS(ON)} with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input / Output Leakage Pb-free lead plating; RoHS compliant
	Applications
	 Lithium-Ion Secondary Batteries Load Switch DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG60N03G	Halogen-Free	TO-263	G	Tape & Reel	800

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parame	ter	Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V _{GS}	±25	V
Drain Current-Continuous	Tc=25°C	1	136 (Silicon limited)	Α
Drain Current-Continuous	Tc=70°C	l _D	109	Α
Drain Current-Pulsed Note 1		I _{DM}	544	Α
Drain Current-Continuous	T _A =25°C	1	16	Α
	T _A =70°C	l _D	12.8	Α
Avalanche Current, L=0.5mH	·	las	26	Α
Avalanche Energy, L=0.5mH		Eas	169	mJ
	Tc=25°C		147	W
Maximum Dawar Dissination	T _C =70°C	D.	94	W
Maximum Power Dissipation	T _A =25°C	P _D	2	W
	T _A =70°C		1.3	W
Storage Temperature Range	<u>.</u>	Tstg	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	RθJA	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	R ₀ JC	Steady State	-	-	0.85	°C/W

1



60V N-Channel Power MOSFET

Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =20A	-	-	4.3	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	3686	-	
Output Capacitance	Coss	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	357	-	pF
Reverse Transfer Capacitance	C _{rss}		-	124	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	12	-	
Rise Time	tr	V _{DS} =30V, I _D =20A, V _{GS} =10V,	-	4	-	
Turn-Off Delay Time	T _{d(off)}	R _{GEN} =3Ω	-	50	-	ns
Fall Time	t _f		-	6	-	
Total Gate Charge at 10V	Qg		-	50	-	
Gate to Source Gate Charge	Q _{gs}	V _{DS} =30V, I _{DS} =20A, V _{GS} =10V	-	15	-	nC
Gate to Drain "Miller" Charge	Q _{gd}		-	2.5	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter Symbol Conditions Min. Typ. Max. Unit						Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _{DS} =20A	-	-	1.3	V
Body Diode Reverse Recovery Time	t _{rr}	1 -20 4 -41/44-400 4 /	-	22	-	ns
Body Diode Reverse Recovery Charge	Qrr	I _F =20A, dl/dt=100A/μs	-	120	-	nC

Notes:

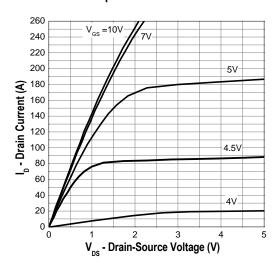
- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design. R_{BJA} shown below for single device operation on FR-4 in still air.



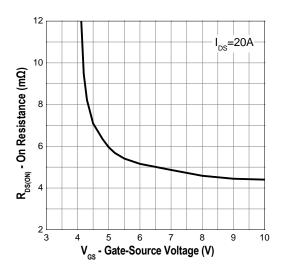
60V N-Channel Power MOSFET

Typical Operating Characteristics

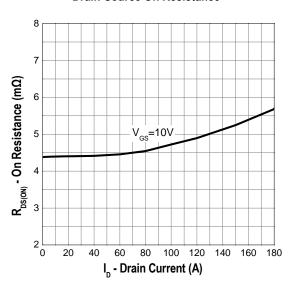
Output Characteristics



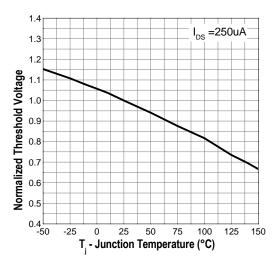
Gate-Source On Resistance



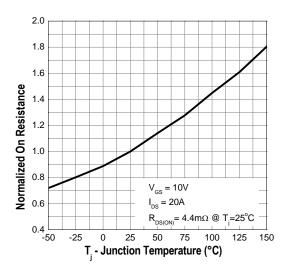
Drain-Source On Resistance



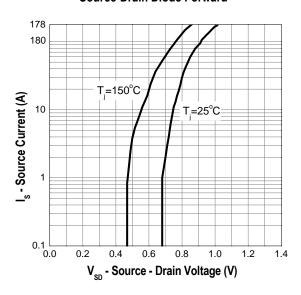
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward

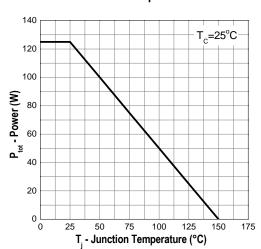




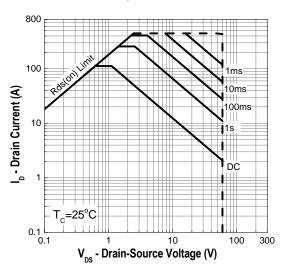
60V N-Channel Power MOSFET

Typical Operating Characteristics (Cont.)

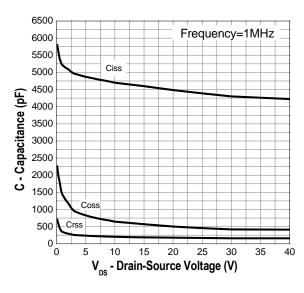
Power Dissipation



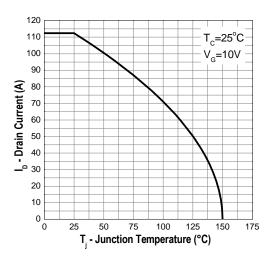
Safe Operation Area



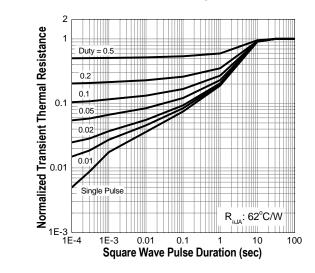
Capacitance



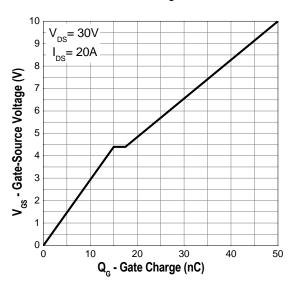
Drain Current



Transient Thermal Impedance



Gate Charge





SG60N03G
60V N-Channel Power MOSFET

Marking Information

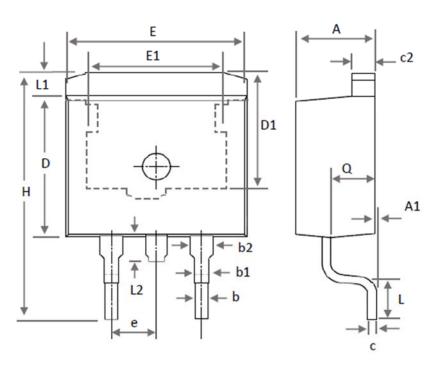
TO-263 (G)	Marking Rule
Laser Marking SG60N03G YYMMXXX	Line 1: Device Name SG60N03G Line 2: Date Code YYMMXXX YY: Year Code MM: Month Code
Diagram	XXX : Serial Number



60V N-Channel Power MOSFET

Package of Dimension

TO-263S



Symbol	Min	Nor	Max	
Α	4.24	4.44	4.64	
A1	0.00	0.10	0.25	
b	0.66	0.76	0.96	
b1	0.76	0.86	1.06	
b2	1.14	1.27	1.47	
С	0.40	0.50	0.60	
c2	1.15	1.30	1.45	
D	8.38	8.60	8.90	
D1	6.86	7.16		
E	9.90	10.20	10.50	
E1		7.80 Ref.		
е		2.54 BSC		
Н	14.61	15.00	15.88	
L	1.78	2.20	2.79	
L1	1.40 REF.			
L2	1.50 REF.			
0	-	2.49	2.70	

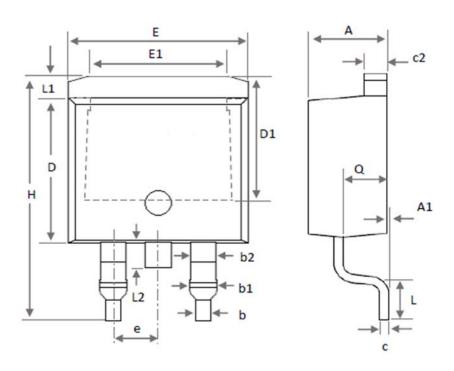


60V N-Channel Power MOSFET

Package of Dimension

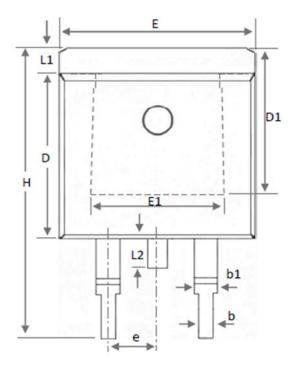
TO-263

G-TYPE



Symbol	Min	Nor	Max
Α	4.24	4.51	4.77
A1	0.00	0.13	0.25
b	0.70	0.83	0.96
b1	1.17	1.46	1.75
b2	1.20	1.45	1.70
С	0.30	0.45	0.60
c2	1.15	1.29	1.42
D	8.50	8.76	9.02
D1	6.60	7.13	7.65
E	9.86	10.11	10.36
E1	6.89	7.39	7.89
e		2.54 BSC	
Н	14.61	15.25	15.88
L	1.78	2.29	2.79
L1	1.07	1.27	1.47
L2	1.40	1.55	1.70
Q	2.30	2.60	2.89

H-TYPE

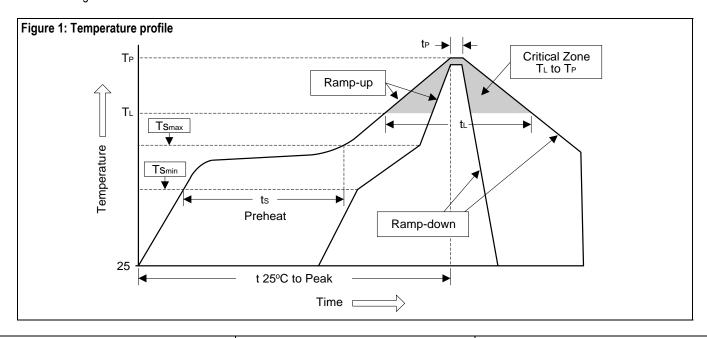




SG60N03G 60V N-Channel Power MOSFET

Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t₂)		
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



SG60N03G
60V N-Channel Power MOSFET

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